



Study on the strain behavior and piezoelectric properties of lead-free $\text{Bi}_{0.5}(\text{Na}_{0.8}\text{K}_{0.2})_{0.5}\text{TiO}_3$ ceramics modified with Sn^{4+} ions

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ABSTRACT

The microstructure, strain behavior, and piezoelectric properties of $\text{Bi}_{0.5}(\text{Na}_{0.8}\text{K}_{0.2})_{0.5}\text{TiO}_3$ (BNKT-Sn) piezoelectric ceramics modified with Sn^{4+} ions were systematically studied. The experimental results indicated that the Sn^{4+} ion doping was a viable and effective method to promote the electromechanical properties and the strain behavior of the BNKT ceramics. When the Sn content was 0.02 mol, the resultant BNKT ceramics exhibited excellent electrical properties with a density of $5.92 \text{ g}\cdot\text{cm}^{-3}$, a dielectric constant (ϵ_r) of 1235, a dielectric loss ($\tan\delta$) of 0.048, the electromechanical coupling factors of 0.36 (k_p) and 0.39 (k_t), a piezoelectric coefficient (d_{33}) of 171 pC/N, and a mechanical quality factor (Q_m) of 125. Moreover, a large unipolar strain of 0.45% and a high normalized strain of 865 pm/V were achieved at 50 °C. The main achievement of this study was the large normalized strain (d_{33}^*) of 876 pm/V at the SnO_2 content of 0.04 mol.

1 Introduction

Lead-free piezoelectric materials with high strains exhibit an interconversion of electrical and mechanical energies that can be utilized in a wide range of applications, such as sensors, actuators, and electrical devices [1–4]. Therefore, multifarious piezoelectric ceramics, such as $\text{K}_x\text{Na}_{(1-x)}\text{NbO}_3$ -based ceramics [5–8], $\text{Bi}_{0.5}(\text{Na}_{(1-x)}\text{K}_x)_{0.5}\text{TiO}_3$ -based piezoelectric ceramics [1, 2, 9–11], and $(\text{Ba}_{1-x}\text{Ca}_x)(\text{Zr}_{1-y}\text{Ti}_y)\text{O}_3$ -based piezoelectric ceramics [12–14] have been synthesized. Among the lead-free materials, $\text{Bi}_{0.5}(\text{Na}_{(1-x)}\text{K}_x)_{0.5}\text{TiO}_3$

(BNKT)-based ceramics are the most promising candidates for replacing the PZT-based piezoelectric ceramics due to the former's large piezoelectric coefficients, large field-induced strains, good ferroelectricity, and high Curie temperatures [15]. Furthermore, modification of the elements at A-and/or B-sites to obtain a modified BNKT solid solution is a viable approach to enhance the dielectric, ferroelectric, and piezoelectric properties or reduce the sintering temperature [16]. Zhang et al. [17] reported that the Sn^{4+} cations could enter the B-sites of a perovskite structure to replace the Ti^{4+} ions and

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enhance the energy storage density. It was also pointed out that 1% mol SnO₂-doped Sr_{0.6}(Na_{0.5}-Bi_{0.5})_{0.4}TiO₃ ceramics yielded a high energy storage efficiency (η) of 80%. Recently, in our research, it was discovered that optimal Sn doping could effectively reduce the sintering temperature of the BNKT ceramics by generating a eutectic liquid phase at 170 °C [18]. Moreover, it was found that isovalent S_n substitution at Ti-sites could induce a ferroelectric-to-nonpolar pseudocubic phase transition and a giant strain at the phase boundary [19, 20]. Recently, several novel BNKT-based ceramics exhibiting high strain under a low electric field have been discovered. In a research reported by Khaliq et al. [21], Bi_{0.5}-Na_{0.5}TiO₃ seed-modified 0.96Bi_{0.5}(Na_{0.78}K_{0.22})_{0.5}-TiO₃-0.04Bi(Mg_{0.5}Ti_{0.5})O₃ exhibited considerably high S_{\max}/E_{\max} values of 725 pm/V at 3 kV/mm and 560 pm/V at 2.5 kV/mm. Gupta et al. [22] recently reported that Sr(Hf_{0.5}Zr_{0.5})O₃-doped Bi_{0.5}(Na_{0.8}-K_{0.2})_{0.5}TiO₃ ceramics display excellent piezoelectric properties. The ceramics with Sr(Hf_{0.5}Zr_{0.5})O₃ content of 2% mol showed the S_{\max}/E_{\max} value of 663 pm/V under the field of 5 kV/mm, indicating its potential as a lead-free replacement material for actuating applications. Huo et al. [23] reported obtaining a large normalized strain of 600 pm/V in the BNKT ceramics in complex with Cs₂Nb₄O₁₁ tungsten bronze phase. Zhang et al. [24] also demonstrated that (Bi_{0.5}Na_{0.5})TiO₃-based ceramics exhibited a large strain of 0.38% ($d_{33}^* = S_{\max}/E_{\max} = 638$ pm/V) under a field of 60 kV/cm. In another report by Zhang et al. [25], $d_{33}^* = S_{\max}/E_{\max} = 720$ was achieved for the NKBT-0.05FN ceramic at 50 kV/cm. In the present study, Sn-modified Bi_{0.5}(Na_{0.8}K_{0.2})_{0.5}TiO₃ (BNKT) lead-free ceramics were synthesized using a conventional solid-state reaction method, with the main objective of improving the strain behavior and the piezoelectric properties of BNKT ceramics by adding a suitable amount of Sn⁴⁺ ions.

2 Experiment

The general chemical formula of the investigated material was Bi_{0.5}(Na_{0.8}K_{0.2})_{0.5}(Ti_{1-x}Sn_x)O₃ (BNKTS) ($x = 0.0, 0.01, 0.02, 0.03,$ and 0.04). Reagent grade oxide powders (purity $\geq 99.5\%$) of Bi₂O₃, TiO₂, Na₂CO₃, K₂CO₃, and SnO₂ were used as starting materials. The oxide powders of Bi₂O₃, TiO₂, Na₂CO₃, K₂CO₃, and SnO₂ were weighed and milled for 20 h.

The powders were calcined at 850 °C for 2 h, producing the BNKTS compound. The production of the BNKTS compound was confirmed through thermogravimetric analysis (TGA) and differential thermal analysis (DTA) [20]. The calcined BNKTS powder was then milled for 20 h. Next, the ground materials were pressed at 150 MPa into pellets of diameter 1.2 cm and thickness 1.5 mm by steel mold of the corresponding diameter, which was then sintered at 1100 °C for 3 h in the air at a heating/cooling rate of 5 °C/min.

The crystalline phase of the sintered ceramics was examined by X-ray diffraction (XRD, D8 Advance) under Cu-K _{α} radiation at a wavelength of 1.5405 Å, in the 2θ range of 20°–70°, and with a step size of 0.02°, at room temperature (RT). Scanning electron microscopy (SEM, Hitachi S₄₈₀₀) was employed to examine the surface morphologies. In addition, the energy-dispersive spectrometry (EDS) of the sintered ceramic was performed. Furthermore, Rietveld refinements were performed using the FullProf software, and the grain size was determined using the mean linear intercept method. The sintered samples were coated with silver paint at 550 °C for 15 min and then polarized in silicone oil at 25–125 °C for 25 min under 3.5 kV/mm to measure their piezoelectric properties. The piezoelectric properties of the Sn-modified BNKT ceramics were determined from their resonant vibration spectra collected at room temperature using an impedance analyzer (HP 4193A and RLC Hioki 3532). The piezoelectric constant, d_{33} , was determined using a d_{33} meter (YE2730A, Sinocera).

3 Results and discussion

3.1 The structure and microstructure characteristics

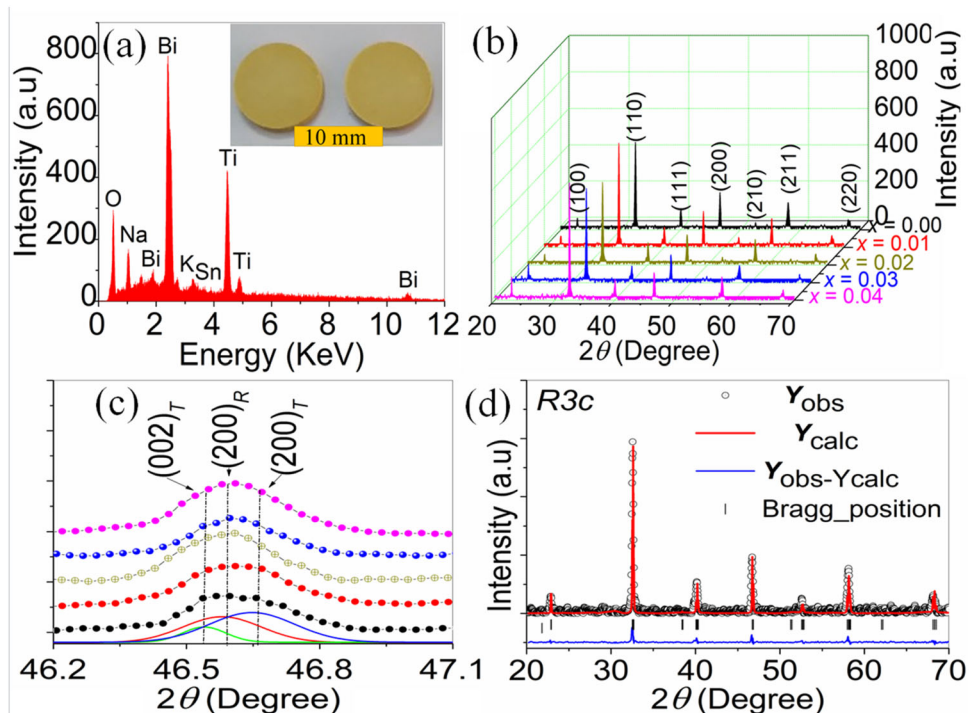
In order to clarify the morphological evolutions and the elemental distributions of the ceramic samples, the EDS spectra of the Sn-doped BNKT ceramics were obtained and are shown in Fig. 1a. It is clear from the EDS spectra that Bi, Na, K, Ti, and O elements were present in the synthesized ceramics, similar to the findings reported by Wang et al. [26]. In our recent research, the sintering temperature of the Sn-doped BNKT ceramics was determined to be 1100 °C [18]. In comparison to the green pellets

without sintering that had a diameter of 12 mm and a thickness of 1.5 mm, after sintering at 1100 °C for 3 h, the Sn-doped BNKT ceramics exhibited good shrinkage with a diameter of 10.3 mm and a thickness of 1.0 mm [inset of Fig. 1a]. Therefore, based on preliminary observation and the testing for sample homogeneity using the EDS surface method, it could be confirmed that the chemical composition of the Sn-doped BNKT ceramics was considerably good qualitatively as well as quantitatively.

Figure 1b displays the crystalline phases of the Sn-doped BNKT ceramics over a 2θ range of 20° – 70° . All samples possessed a typical perovskite structure. In order to clearly illustrate the effect of SnO_2 on the structural properties of the BNKT ceramics, a magnified view of the peaks in the region between 46.2° and 47.1° is presented in Fig. 1c. The tetragonal phase concentration was quite low and was observed only in the ceramic samples without Sn^{4+} ions or those with an extremely small concentration of Sn^{4+} ions. The Lorentz curves could be used to theoretically fit the partial intensity profile of ceramics as presented in Fig. 1c. This was consistent with the report by Han et al. [27] for Sn-doped $\text{Bi}_{1/2}(\text{Na}_{0.82}\text{K}_{0.18})_{1/2}\text{TiO}_3$. Moreover, the presence of rhombohedral crystal symmetries ($R3c$) in the $\text{Bi}_{0.5}(\text{Na}_{0.8}\text{K}_{0.2})_{0.5}(\text{Ti}_{0.98}\text{Sn}_{0.02})\text{O}_3$ sample was confirmed using the

Rietveld refinement technique (Fig. 1d). The fitting analysis of the peak shape, peak position, structure, and background was performed by considering the rhombohedral ($R3c$) space group symmetry. In our previous report, the coexistence of two different structural phases occurred, and hence, the morphotropic phase boundary (MPB) was confirmed at Sn^{4+} ion content of 0–0.01 mol, along with the rhombohedral phase fraction ($R3c$) of greater than 60% [20]. On further refinement (the content of Sn^{4+} ions was higher than 0.01 mol), the rhombohedral symmetry was observed to fit well ($M_R = 100\%$). It is well known that the $\text{Bi}_{0.5}\text{Na}_{0.5}\text{TiO}_3$ ceramic is rhombohedral, while the $\text{Bi}_{0.5}\text{K}_{0.5}\text{TiO}_3$ ceramic is tetragonal at room temperature [28]. The split $(002)_T$ and $(200)_T$ peaks indicate the ferroelectric tetragonal phase (T), while the single $(200)_R$ peak represents the ferroelectric rhombohedral phase (R). Thus, doping could increase the tetragonal or rhombohedral phases of the BNKT ceramic system. According to Pradhan et al. [29], the structure of the $\text{Bi}_{0.5}(\text{Na}_{0.8}\text{K}_{0.2})_{0.5}\text{TiO}_3$ ceramics can be described by the $P4mm$ space group with the lattice parameters of $a = 3.893 \text{ \AA}$ and $c = 3.908 \text{ \AA}$ and a c/a ratio of 1.004. However, in our work, a pure $\text{Bi}_{0.5}(\text{Na}_{0.8}\text{K}_{0.2})_{0.5}\text{TiO}_3$ with both R phase (space group $R3c \sim 60\%$) and T phase (space group $P4mm \sim 40\%$) was observed [20]. Similar

Fig. 1 The structure of the SnO_2 -doped BNKT ceramics



observations were reported by Ullah et al. [28], who observed that the relative amount of the tetragonal phases was 58.6% for the $\text{Bi}_{0.5}(\text{Na}_{0.78}\text{K}_{0.22})_{0.5}\text{TiO}_3$ ceramic samples sintered at 1100 °C. The overall effect of Sn^{4+} ions on the XRD patterns of $\text{Bi}_{0.5}(\text{Na}_{0.8}\text{K}_{0.2})_{0.5}\text{TiO}_3$ ceramics was the slight shift in the intensity of the peaks toward lower angles and the enhancement of the rhombohedral phase (R) structure, as depicted in Fig. 1c. This result implies that the Sn^{4+} ions (0.69 Å) replaced the similar-sized Ti^{4+} ions (0.61 Å) at the B-site rather than the bigger cations at the A-site, such as K^+ , Na^+ , and Bi^{3+} [18]. Similar results were observed by Yan et al. [30] in Sn-doped $\text{Ba}_{0.5}\text{Sr}_{0.5}\text{TiO}_3$ ceramics as well as by Zhang et al. [17] in Sn-doped $\text{Sr}_{0.6}(\text{Na}_{0.5}\text{Bi}_{0.5})_{0.4}\text{TiO}_3$ ceramics. It is evident that the Goldschmidt's tolerance factor [16], $t_{(\text{BNKT}/\text{Sn})} \leq t_{\text{BNKT}}$ when $r_{\text{Ti}} = 0.61 \text{ \AA} < r_{\text{Sn}} = 0.69 \text{ \AA}$, and the corresponding atom radii are $r_{\text{Bi}^{3+}} = 1.17 \text{ \AA}$, $r_{\text{Na}^+} = 1.39 \text{ \AA}$, $r_{\text{K}^+} = 1.64 \text{ \AA}$, and $r_{\text{O}^{2-}} = 1.42 \text{ \AA}$ [31, 32]. Therefore, the tolerance factor of pure BNKT was $t_{\text{BNKT}} = 0.9492$ when $t_{\text{BNKT}/\text{Sn}} \leq t_{\text{BNKT}} < 1$.

Figure 2 presents the scanning electron microscopy images of the fracture surfaces (SEM) of the Sn-doped BNKT ceramics with different Sn contents. In our previous research [18], the perovskite structure of the ceramic samples was formed in the temperature range of 745–883 °C. In order to ensure the single perovskite phase formation in high-volume samples, the calcination of the Sn-doped BNKT ceramics was carried out at 850 °C for two hours (Fig. 2a). The average grain size of the calcined BNKT compounds was about 0.33 μm (Fig. 2a). However, the mechanism underlying the effects of the preliminary calcination temperature on the microstructures of the Sn-doped BNKT samples remains unknown so far and requires further investigation. In order to better understand the influences of different Sn contents on the microstructure of the Sn-doped BNKT ceramics, the samples were sintered at 1100 °C for three hours (Fig. 2b–f). In all samples, the grains had a dense microstructure and a clear grain boundary. At low Sn doping levels ($x \leq 0.03$), the grain size increased with the increasing Sn content and reached the maximum value of 1.62 μm at the Sn content of 0.03 mol (Fig. 3e). The increase in the grain size may be due to a reaction between Bi and Sn elements, which produced some molten compounds [33, 34]. Similar behaviors of increase in the grain size and change in the morphology have also been observed in Zn-

modified BNKT ceramics [35]. Muhsen et al. [36] suggested that the increase in the grain size could be related to the differences in the ionic radii of Sn^{4+} and Ti^{4+} at the B-sites, due to which the interdiffusion movement occurred via the grain boundary through the formation of necks between the grains, and its growth accelerated the grain growth. As the Sn content further increased, the grain size decreased (Fig. 3f). This could be because during sintering to produce the Sn-modified BNKT ceramics, a portion of Sn^{4+} ions may accumulate near the grain boundaries and reduce their densification mobility. The reduction in the mobility of the grain boundary weakens the mass transport and thus inhibits the grain growth to a certain extent [37]. It is reported that a large grain size is essential to obtain ceramics with good piezoelectric properties [16, 18, 36]. Sn^{4+} ions diffused into the BNKT lattice until the Sn doping content was less than 4%.

3.2 Influence of Sn content on the strain behavior and piezoelectric properties of BNKT ceramics

Figure 4a illustrates the dielectric constant (ϵ_r) and dielectric loss ($\tan\delta$) of the sintered ceramics with different SnO_2 contents at 1 kHz. With the increasing Sn content, ϵ_r gradually increased, reached the peak value of 1235 at $x = 0.02$, and then decreased. The variation trend of $\tan\delta$ was the opposite; $\tan\delta$ decreased rapidly when the Sn content was less than 0.02 mol, reached the smallest value of 0.048 at the Sn content of 0.02 mol, and then started to increase.

These phenomena are probably related to the density and the increasing grain size. According to Muhsen et al. [36], the movement and growth of the grain boundaries through the formation of necks between the grains increase the grain size of the ceramics. The dielectric properties of the Sn-doped BNKT ceramics were improved with an increase in their density (Fig. 4b). With the increase in the Sn content from 0 to 0.04 mol, the density of the ceramics increased from 5.80 g/cm^3 to 5.92 g/cm^3 , reached the maximum values of 5.92 g/cm^3 at $x = 0.02$ (98.6% of the theoretical density) corresponding to the highest ϵ_r value, and then started to decrease again. This could be because the low melting point of the Bi–Sn system is beneficial for the generation of a eutectic liquid phase at 138.4 °C [33, 34], and this phase can work as a lubricant

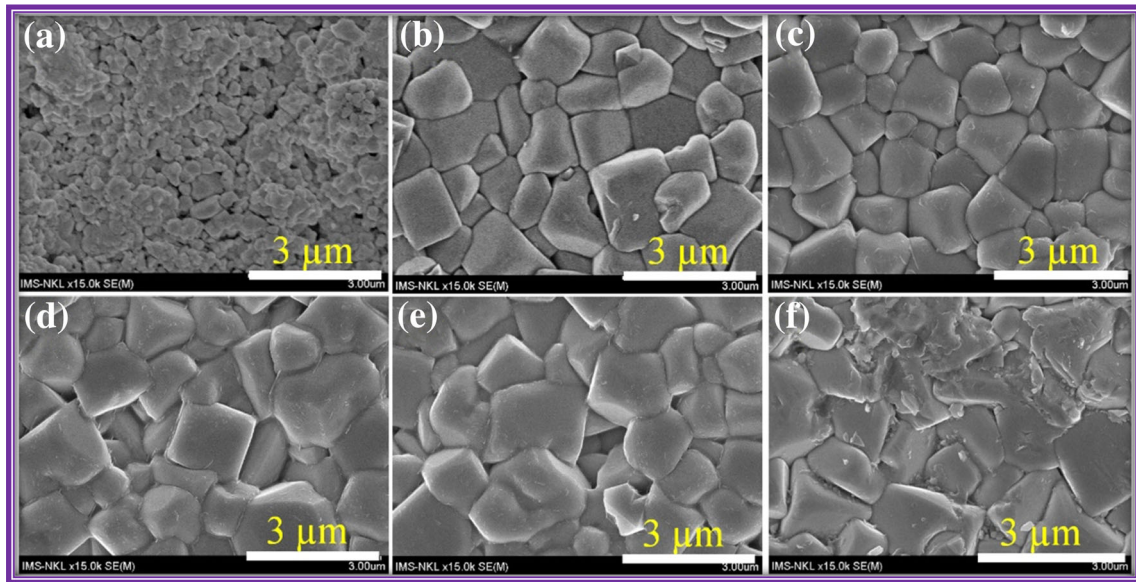


Fig. 2 Microstructures of the Sn-doped BNKT ceramics: **a** calcined ceramic at 850 °C, **b-f** sintered ceramic at 1100 °C (**b** $x = 0.00$, **c** $x = 0.01$, **d** $x = 0.02$, **e** $x = 0.03$, **f** $x = 0.04$)

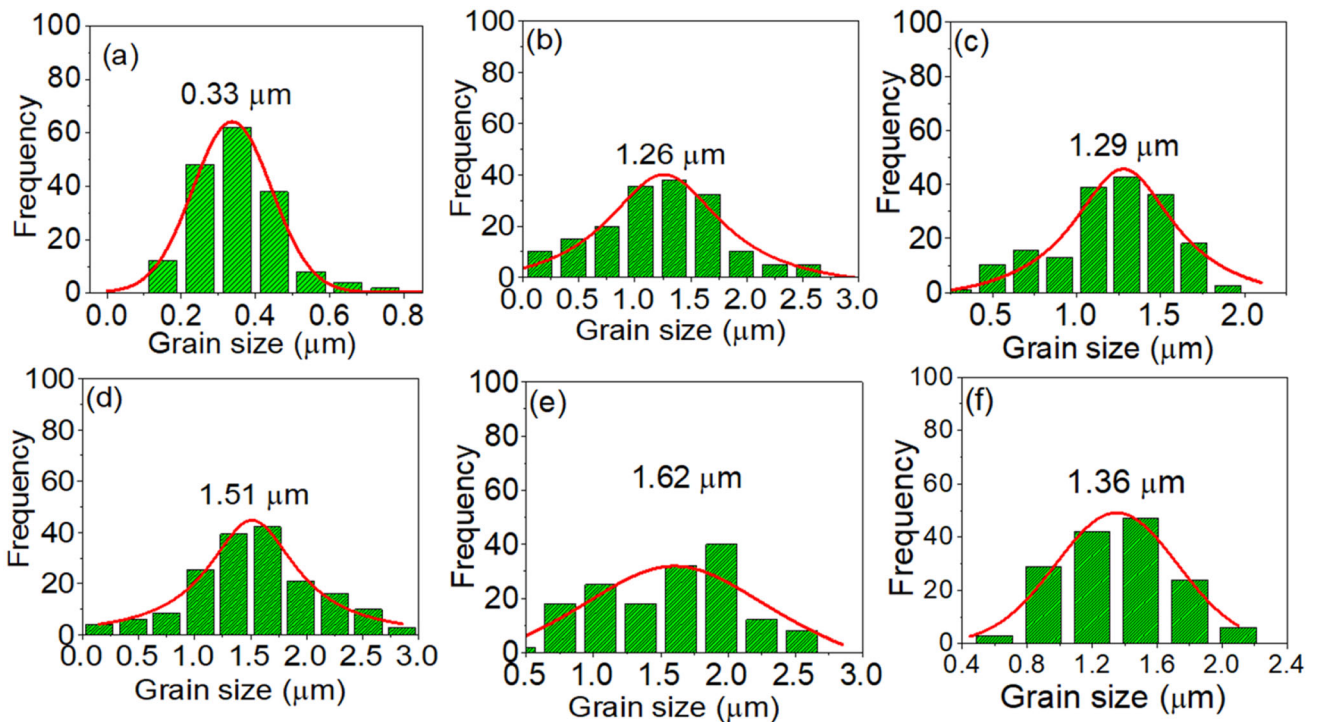


Fig. 3 Grain size distribution for the SnO₂-doped BNKT ceramics: **a** calcined ceramic at 850 °C, **b-f** sintered ceramic at 1100 °C (**b** $x = 0.00$, **c** $x = 0.01$, **d** $x = 0.02$, **e** $x = 0.03$, **f** $x = 0.04$)

during the sintering process, wetting the solid particles, and providing capillary pressure among them, thereby increasing the sintering capacity of the ceramics [3, 4, 38]. However, when the Sn content exceeded the solubility limit of the Sn⁴⁺ ions, the

segregation of some Sn⁴⁺ ions at the grain boundaries prevented grain boundary movements during sintering and inhibited the grain growth, leading to a decrease in the grain size and a reduction in the

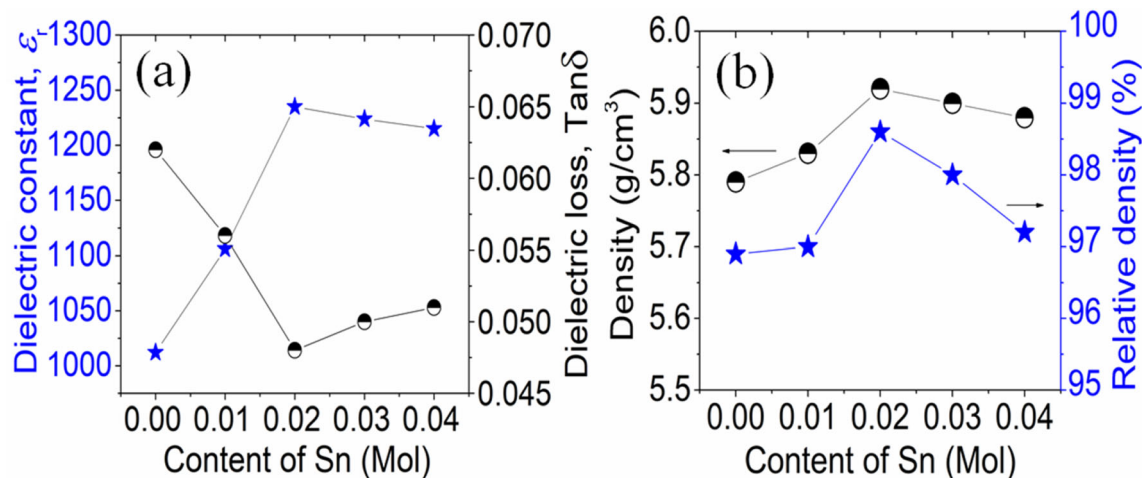


Fig. 4 **a** The dielectric constant and dielectric loss of the Sn-doped BNKT ceramics; **b** Density of the Sn-doped BNKT ceramics

density and the dielectric properties of the ceramics [36].

The piezoelectric properties of the Sn-modified BNKT ceramics were determined from their resonant vibration spectra (Fig. 5a, b). It is clear from Fig. 5c that the electromechanical coupling factors (k_p , k_t) and the piezoelectric factor (d_{33}) varied as a function of the Sn content. With the increase in the Sn content, the values of k_p , k_t and d_{33} were significantly increased. At $x = 0.02$, the Sn-modified BNKT ceramics exhibited the best piezoelectric properties, with the k_p , k_t , and d_{33} values of 0.36, 0.39, and 171 pC/N, respectively, and this could be attributed to the increase in the grain size. Therefore, at small Sn contents, the increase in the grain size was beneficial for the improvement of k_p , k_t , and d_{33} as the increasing grain size reduced the volume fraction of the grain boundaries [36]. However, with further increase in the Sn content, the values of k_p , k_t , and d_{33} decreased; this happened when the solubility limit of the Sn^{4+} ions in the $\text{Bi}_{0.5}(\text{Na}_{0.8}\text{K}_{0.2})_{0.5}\text{TiO}_3$ ceramics was 0.02 mol. When the SnO_2 content was above 0.02 mol, excess Sn^{2+} ions accumulated at the grain boundaries and abnormally influenced the piezoelectric properties. Jiang et al. [39] obtained the best piezoelectric properties with $k_p = 0.3$ in 0.2 wt% Mn^{2+} doped $(\text{Na}_{0.5}\text{K}_{0.2})_{0.5}\text{Bi}_{0.5}\text{TiO}_3$. Zhang et al. [40] reported that 0.3 wt.% Sm^{3+} substitution in $(\text{Na}_{0.82}\text{K}_{0.18})\text{Bi}_{0.5}\text{TiO}_3$ ceramics exhibited a high planar coupling factor (k_p) value of 0.22. Surprisingly, the variation in the mechanical quality factor (Q_m) was almost similar to that of d_{33} , and the optimized Sn content was 0.03 mol instead of 0.02 mol, resulting in

the highest Q_m value of 125 (Fig. 5b). The values of Q_m increased when the Sn content increased from 98 to 125, and then decreased with a further increase in the Sn content. It is believed that mechanical loss is typically quantified in terms of the material's mechanical loss tangent ($\tan\delta$) and the dielectric loss is also quantified in terms of the material's dielectric loss tangent ($\tan\delta$), which occur in the material due to the inertia of the charge exchange process [41, 42], which is represented by $Q^{-1} m \sim \tan\delta$. Interestingly, an abrupt drop in the Q_m value was observed when 0.04 mol Sn^{4+} ions were doped on the B-site Ti^{4+} ions. The accumulation of an excess amount of Sn ions at grain boundaries led to a reduction in the mechanical quality factor (Fig. 3f) [43]. Thus, although the average grain size of the ceramic was the largest when the Sn content reached $x = 0.03$ (1.62 μm), as depicted in Fig. 3e, the piezoelectric properties of Sn-doped BNKT ceramics reached the highest values of k_p , k_t , d_{33} , and Q_m when $\text{Bi}_{0.5}(\text{Na}_{0.8}\text{K}_{0.2})_{0.5}\text{TiO}_3$ was doped with 2 mol.% of the Sn dopant.

Figure 6 demonstrates the bipolar strain curves of the BNKT ceramics as a function of the Sn content [44]. A slight decrease in the maximum strain (S_{max}) occurred initially at $x = 0.01$; then, the S_{max} value increased with a further increase in the Sn content (Fig. 7a). The value of S_{neg} increased with the increasing Sn content and reached the maximum value of 0.16% at $x = 0.02$. Negative strains in ferroelectric materials manifest as the switching back point of domain reorientation under cyclic fields; hence, the highest values of k_p and d_{33} were obtained

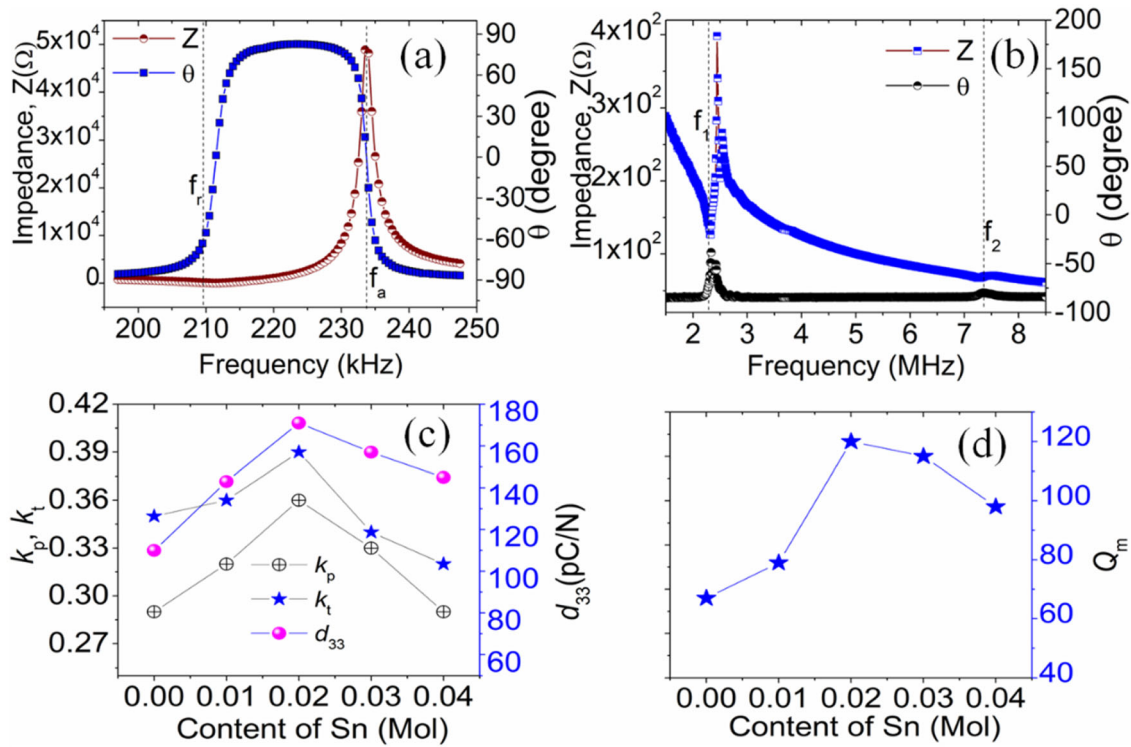


Fig. 5 **a** Radial and **b** Thickness resonant spectra of $\text{Bi}_{0.5}(\text{Na}_{0.8}\text{K}_{0.2})_{0.5}(\text{Ti}_{0.98}\text{Sn}_{0.02})\text{O}_3$ ceramics; **c** The values k_p , k_t , and d_{33} ; **d** The values of Q_m as a function of Sn doping

at $x = 0.02$. However, with further increase in the Sn content, the S_{neg} value decreased and tended to zero because the relaxor of the Sn-doped BNKT ceramics was enhanced [44]. The normalized strains (d_{33}^*) of the sintered ceramics were calculated (Fig. 7a) and compared with those of the other BNKT-based piezoceramics (Fig. 7b). It is evident from Fig. 7a that

the normalized strain reached the maximum value of 876 pm/V at $x = 0.04$ and then decreased. Therefore, the variation of the normalized strain with the Sn content was almost similar to that of S_{max} , and the optimized Sn content of 0.04 mol led to the largest d_{33}^* value of 876 pm/V (Fig. 7a). Among all the BNKT-based ceramics reported to date, the BNKT-0.04Sn ceramic has the largest d_{33}^* value of 876 pm/V (Fig. 7b) [45–50].

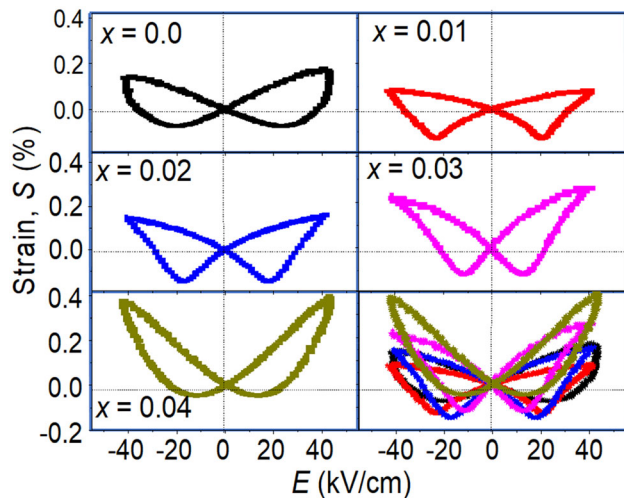
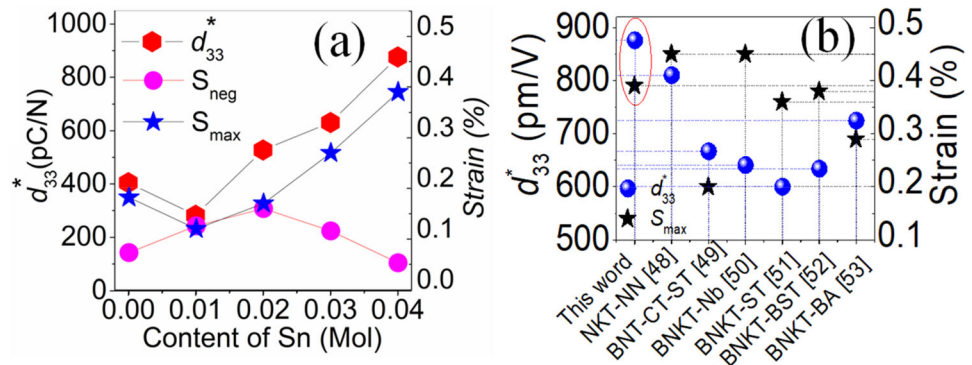


Fig. 6 The bipolar $S - E$ loop of BNKT ceramics as a function of Sn doping

3.3 Influence of temperature on the strain behavior and piezoelectric properties of BNKT ceramics

For practical applications of piezoelectric materials, the temperature stability of their electromechanical properties (poling temperature and operating temperature) is crucial. In order to determine the optimum poling temperature for the Sn-doped BNKT ceramics to enhance their piezoelectric responses, their poling temperatures were measured in silicone oil under 3.5 kV/mm for 25 min (Fig. 8). At the poling temperature of 75 °C, BNKT-0.02Sn exhibited the best piezoelectric properties with $d_{33} = 171$ pC/N and $k_p = 0.36$. The effect of temperature allowed the

Fig. 7 **a** Maximum strain (S_{\max}), negative strain (S_{neg}), normalized strain (d_{33}^*) versus Sn content; **b** Comparison of S_{\max} and d_{33}^* values among the reported BNKT-based bulk ceramics



flexible domains to easily move in the field direction and resulted in improved piezoelectric properties. The suitable polarization of the Sn-doped BNKT ceramics was noticed in the temperature range of 50–100 °C, which then decreased quickly upon further increasing the temperature [51–53]. With a further increase in the temperature, the rise of the leakage current caused a reduction in d_{33} and k_p [12], which proves that the piezoelectric responses of the ceramics were dependent on the poling temperature.

Figure 9 displays the temperature-dependent strain hysteresis loops of the $\text{Bi}_{0.5}(\text{Na}_{0.8}\text{K}_{0.2})_{0.5}(\text{Ti}_{0.98}\text{Sn}_{0.02})\text{O}_3$ ceramics ($x = 0.02$). A typical ferroelectric behavior was noticed until 100 °C. However, when the temperature exceeded $T_{\text{F-R}}$ (Fig. 10) and reached 125 °C, a little negative strain was observed [48]. Several researchers have suggested that the shift of $T_{\text{F-R}}$ in various lead-free BNKT ceramics could be related to the loss of Bi, K, and/or Na during the processing [20]. It is believed that the origin of the large strain in Bi-based ceramics is associated with the reversible electric field-induced phase transition

from a nonpolar ergodic relaxor to the polar ferroelectric state [22]. Therefore, the temperature dependence of the polarization and the strain hysteresis are the maximum at the boundary where the ferroelectric state transforms into the relaxor state.

In order to elucidate the variation trend of temperature-dependent strains, strain values were plotted against temperatures ranging from 25 °C to 125 °C (Fig. 11). The temperature-induced phase transition of the ceramics was verified by the strain–electric field (S–E) hysteresis measurements. The positive maximum strain (S_{\max}) gradually increased with temperature, reached the highest value of 0.45% at 50 °C, and then gradually decreased (Fig. 11). With further increase in temperature, lattice softening occurred when the temperature approached the phase transition temperature; hence, the S_{\max} value decreased [54]. When the sintering temperature was higher than $T_{\text{F-R}}$, a notable increase in the usable strain occurred due to the reduction in the remanent strain (Fig. 9). According to Yin et al. [55], S_{\max} reached the maximum value and S_{neg} dropped to almost zero at around $T_{\text{F-R}}$, indicating that the field-induced long-range ferroelectric order disappeared around this temperature.

It is evident from Fig. 11b that $\text{Bi}_{0.5}(\text{Na}_{0.8}\text{K}_{0.2})_{0.5}(\text{Ti}_{0.98}\text{Sn}_{0.02})\text{O}_3$ ceramic presented the highest d_{33}^* value of 865 pm/V at 50 °C. The positive maximum strain (S_{\max}) gradually increased with increasing temperature and promoted the increase in d_{33}^* according to the following formula: $d_{33}^* = S_{\max}/E_{\max}$ [45, 51]. The obtained d_{33}^* and S_{\max} values in this research are higher than those reported previously for lead-free ceramics [19]. The large S_{\max} value can be attributed to the reversible electric field-induced transition between the ergodic relaxor and the ferroelectric status around the $T_{\text{F-R}}$ temperature [48].

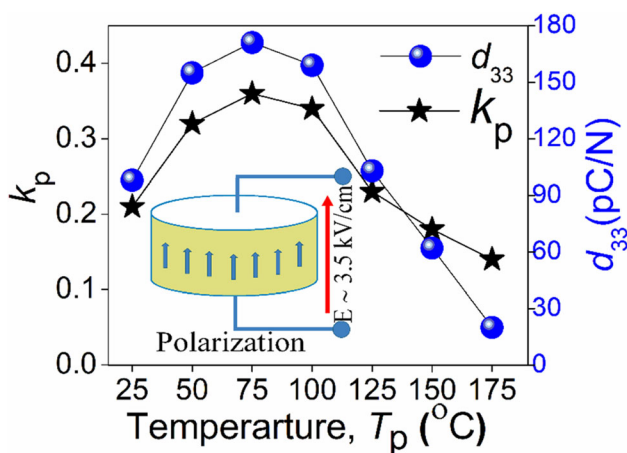


Fig. 8 Poling temperature dependence of BNKT-0.02Sn ceramics

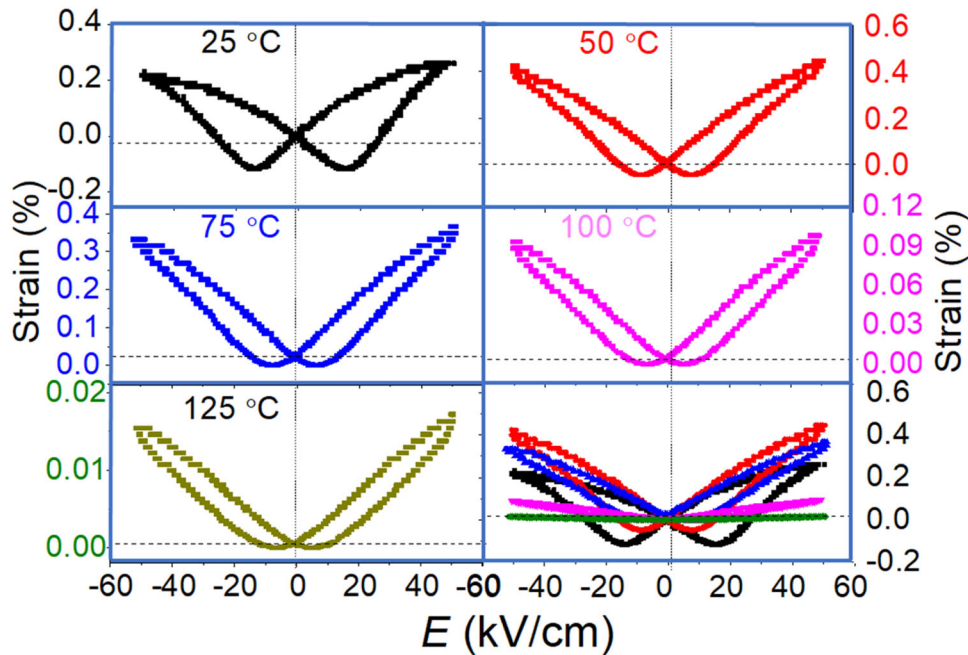


Fig. 9 Plots of strain vs. electric field for $\text{Bi}_{0.5}(\text{Na}_{0.8}\text{K}_{0.2})_{0.5}(\text{Ti}_{0.98}\text{Sn}_{0.02})\text{O}_3$ ceramics at various temperatures

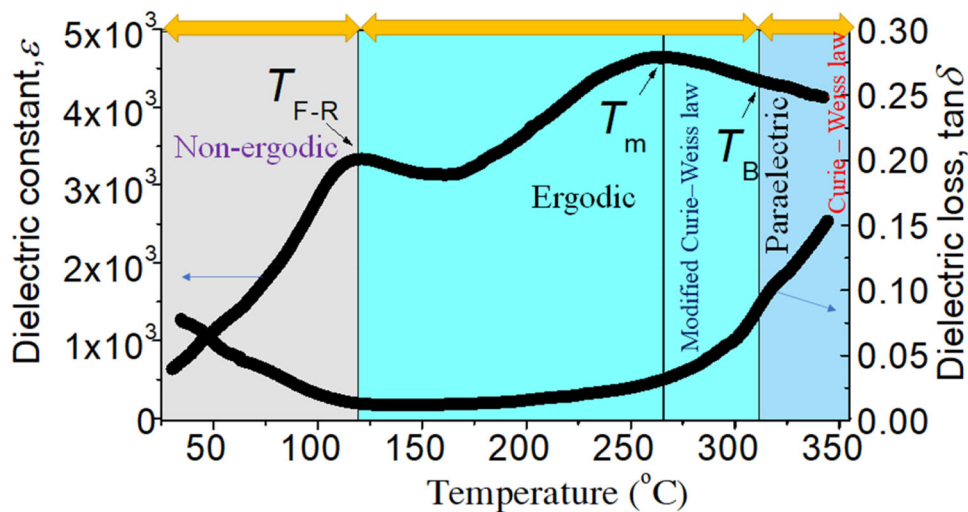


Fig. 10 Temperature dependence of the dielectric constant and the loss of $\text{Bi}_{0.5}(\text{Na}_{0.8}\text{K}_{0.2})_{0.5}(\text{Ti}_{0.98}\text{Sn}_{0.02})\text{O}_3$ ceramics as the functions of temperature, measured at 1 kHz

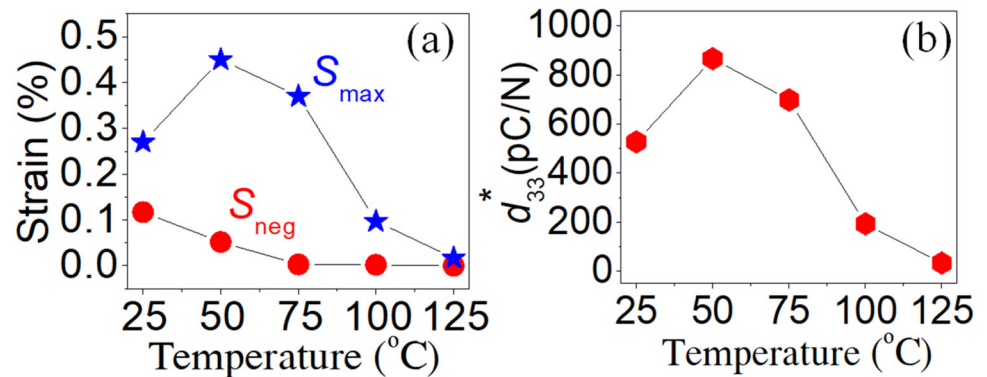
Due to the shift of T_{F-R} below the room temperature (RT), a large d_{33}^* was obtained at RT .

4 Conclusions

In this work, $\text{Bi}_{0.5}(\text{Na}_{0.8}\text{K}_{0.2})_{0.5}(\text{Ti}_{1-x})\text{Sn}_x\text{O}_3$ lead-free ceramics were synthesized using a conventional mixed-oxide approach. The experimental results revealed that the doping of Sn^{4+} ions into the BNKT

ceramics significantly improved their dielectric and piezoelectric properties as well as their strain behavior. The resultant ceramics exhibited excellent dielectric properties with a density of $5.92 \text{ g}\cdot\text{cm}^{-3}$, a dielectric constant (ϵ_r) of 1235, and a dielectric loss ($\tan\delta$) of 0.048. Under the optimized poling temperature, the sintered ceramics had the best piezoelectric constant (d_{33}) of 171 pC/N, while the electromechanical coupling factors were 36% (k_p) and 39% (k_t) at 75 °C. In particular, the electric field-induced

Fig. 11 a S_{\max} and S_{neg} and b d_{33}^* as a function of temperature



unipolar strain was increased from 0.17% for the pure BNKT ($x = 0.00$) to 0.45% ($x = 0.02$) at an electric field of 50 kV/cm, with a corresponding increase in the large normalized strain (d_{33}^*) from 400 to 876 pm/V for 4 mol. % Sn-modified BNKT ceramic, which is relevant for the actuator applications of this material.

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Author contributions

All persons who meet authorship criteria are listed as authors, and all the authors certify that they have participated sufficiently in the work to take public responsibility for the content, including participation in the concept, design, analysis, writing, or revision of the manuscript.

References

- L.D. Vuong, D.A. Quang, P. Van Quan, N. Truong-Tho, J. Electron. Mater. **49**(11), 6465–6473 (2020)
- L.D. Vuong, D.A. Quang, V.T. Tung, N.H. Chuc, N.N. Trac, J. Mater. Sci.: Mater. Electron. **31**(20), 18056–18069 (2020)
- L.D. Vuong, P.D. Gio, N.D.V. Quang, T.D. Hieu, T.P. Nam, J. Electron. Mater. **47**(10), 5944–5951 (2018)
- L.D. Vuong, V.T. Tung, P.D. Gio, The Investigation on the Fabrication and Characterization of the Multicomponent Ceramics Based on PZT and the Relaxor PZN-PMnN Ferroelectric Materials, Ceramic Materials, IntechOpen2020
- X. Lv, J. Wu, X.-X. Zhang, Chem. Eng. J. **402**, 126215 (2020)
- W. Wu, J. Ma, B. Wu, Q. Gou, M. Chen, J. Alloys Compds. **822**, 153585 (2020)
- Y. Pan, X. Dai, J. Li, Y. Yi, Y. Yu, C. He, Y. Liu, Y. Xiang, Y. Chen, Phys. Scr. **95**(6), 065802 (2020)
- P.D. Gio, H.Q. Viet, L.D. Vuong, Int. J. Mater. Res. **109**(11), 1071–1076 (2018)
- D.V. Le, A.Q. Dao, J. Electroceram. **44**(1), 68–77 (2020)
- X. Zhao, W. Bai, Y. Ding, L. Wang, S. Wu, P. Zheng, P. Li, J. Zhai, J. Eur. Ceram. Soc. **40**(13), 4475–4486 (2020)
- W. Kang, Y. Li, Z. Zheng, R. Zhao, Ceram. Int. **46**(11 Part A), 18089–18095 (2020)
- D.A. Tuan, V.T. Tung, L.D. Vuong, N.H. Yen, L.T.U. Tu, Journal of Elec Materi **47**(10), 6297–6301 (2018)
- D.A. Tuan, L.D. Vuong, V.T. Tung, N.N. Tuan, N.T. Duong, J. Ceram. Process. Res. **19**(1), 32–36 (2018)
- S. Shi, H. Hashimoto, T. Sekino, Ceram. Int. **47**(3), 3272–3278 (2020)
- J. Rödel, W. Jo, K.T.P. Seifert, E.M. Anton, T. Granzow, D. Damjanovic, J. Am. Ceram. Soc. **92**(6), 1153–1177 (2009)
- L.D. Vuong, P.D. Gio, J. Alloys Compds. **817**, 152790 (2020)
- L. Zhang, Z. Wang, Y. Li, P. Chen, J. Cai, Y. Yan, Y. Zhou, D. Wang, G. Liu, J. Eur. Ceram. Soc. **39**(10), 3057–3063 (2019)
- N. Truong-Tho, L.D. Vuong, J. Adv. Dielectr. **10**(04), 2050011 (2020)
- J.-S. Lee, K.-N. Pham, H.-S. Han, H.-B. Lee, V.D.N. Tran, J. Korean Phys. Soc. **60**(2), 212–215 (2012)
- N. Truong-Tho, J. Electroceram. (2020). <https://doi.org/10.1007/s10832-020-00224-5>
- A. Khaliq, M. Sheeraz, A. Ullah, J.S. Lee, C.W. Ahn, I.W. Kim, Sens. Actuators A **258**, 174–181 (2017)
- S.K. Gupta, R. McQuade, B. Gibbons, P. Mardilovich, D.P. Cann, J. Appl. Phys. **127**(7), 074104 (2020)
- Z. Huo, H. Wang, J. Xu, G. Rao, J. Wang, C. Zhou, C. Yuan, Ceram. Int. **46**(8), 10067–10074 (2020)
- H. Zhang, P. Xu, E. Patterson, J. Zang, S. Jiang, J. Rödel, J. Eur. Ceram. Soc. **35**(9), 2501–2512 (2015)
- Y. Zhang, P. Fan, H. Fan, B. Ye, G. Zhang, S. Jiang, H. Zhang, J. Electroceram. **44**(1), 32–40 (2020)

26. T. Wang, X.-M. Chen, Y.-Z. Qiu, *Ferroelectrics* **510**(1), 161–169 (2017)
27. H.-S. Han, W. Jo, J.-K. Kang, C.-W. Ahn, I. Won Kim, K.-K. Ahn, J.-S. Lee, *J. Appl. Phys.* **113**(15), 154102 (2013)
28. A. Ullah, C.W. Ahn, A. Hussain, I.W. Kim, *Curr. Appl. Phys.* **10**(6), 1367–1371 (2010)
29. L.K. Pradhan, R. Pandey, S. Kumar, S. Kumari, M. Kar, *J. Mater. Sci.: Mater. Electron.* **30**(10), 9547–9557 (2019)
30. Y. Yan, Q. Wu, Y. Yang, L. Zhang, H. Lin, G. Xue, X. Liu, Y. Chen, J. Yang, G. Liu, *Ferroelectrics* **520**(1), 171–176 (2017)
31. Y. Tsur, T.D. Dunbar, C.A. Randall, *J. Electroceram.* **7**(1), 25–34 (2001)
32. S.K. Ghosh, V. Chauhan, A. Hussain, S.K. Rout, *Ferroelectrics* **517**(1), 97–103 (2017)
33. I. Manasijević, L. Balanović, T.H. Grgurić, D. Minić, M. Gorgievski, *Mater. Res.* (2018). <https://doi.org/10.1590/1980-5373-mr-2018-0501>
34. J. Vizdal, M.H. Braga, A. Kroupa, K.W. Richter, D. Soares, L.F. Malheiros, J. Ferreira, *Calphad* **31**(4), 438–448 (2007)
35. L.D. Vuong, N. Truong-Tho, *J. Electron. Mater.* **46**(11), 6395–6402 (2017)
36. K.N.D.K. Muhsen, R.A.M. Osman, M.S. Idris, M.H.H. Jumali, N.H.B. Jamil, *J. Mater. Sci.: Mater. Electron.* **30**(23), 20654–20664 (2019)
37. W. Li, J. Hao, J. Du, P. Fu, W. Sun, C. Chen, Z. Xu, R. Chu, *J. Adv. Ceram.* **9**(1), 72–82 (2020)
38. P.D. Gio, H.T.T. Hoa, *J. Mater. Sci. Chem. Eng.* **2**(11), 20 (2014)
39. X.P. Jiang, L.Z. Li, F.L. Jiang, Y.Y. Zheng, L.H. Liu, Effects of Mn-doping on the piezoelectric and ferroelectric properties of (Na_{0.8}K_{0.2})_{0.5}Bi_{0.5}TiO₃ ceramics, *Trans Tech Publ*, pp. 69–71.
40. Y. Zhang, R. Chu, Z. Xu, J. Hao, Q. Chen, F. Peng, W. Li, G. Li, Q. Yin, *J. Alloy. Compd.* **502**(2), 341–345 (2010)
41. M.G.S. Ali, N.Z. Elsyed, A.M. Abdel Fattah, G.A. Ali, *Journal of Computational Electronics* **11**(2), 196–202 (2012).
42. H. Chen, B. Tang, C. Zhong, Y. Yuan, Y. Tan, S. Zhang, *Ceram. Int.* **43**(10), 7383–7386 (2017)
43. L.D. Vuong, P.D. Gio, *J. Mod. Phys.* **5**(14), 1258–1263 (2014)
44. Z. Huo, H. Xie, J. Xu, L. Yang, W. Qiu, X. Zhang, C. Zhou, H. Wang, *Front. Mater.* **7**, 8 (2020)
45. G. Dong, H. Fan, J. Shi, M. Li, *J. Am. Ceram. Soc.* **98**(4), 1150–1155 (2015)
46. H.T.K. Nguyen, T.A. Duong, F. Erkinov, H. Kang, B.W. Kim, C.W. Ahn, H.-S. Han, J.-S. Lee, *J. Korean Ceram. Soc.* **57**(5), 570–577 (2020)
47. K.-N. Pham, A. Hussain, C.W. Ahn, W.K. Ill, S.J. Jeong, J.-S. Lee, *Mater. Lett.* **64**(20), 2219–2222 (2010)
48. K. Wang, A. Hussain, W. Jo, J. Rödel, *J. Am. Ceram. Soc.* **95**(7), 2241–2247 (2012)
49. A. Ullah, R.A. Malik, A. Ullah, D.S. Lee, S.J. Jeong, J.S. Lee, I.W. Kim, C.W. Ahn, *J. Eur. Ceram. Soc.* **34**(1), 29–35 (2014)
50. D.S. Lee, D.H. Lim, M.S. Kim, K.H. Kim, S.J. Jeong, *Appl. Phys. Lett.* **99**(6), 062906 (2011)
51. S.-J. Jeong, D.-S. Lee, M.-S. Kim, S.-M. Jang, I.-S. Kim, S. Mohsin, J.-S. Song, *J. Electroceram.* **33**(3–4), 230–238 (2014)
52. K. Kumar, B.K. Singh, M.K. Gupta, N. Sinha, B. Kumar, *Ceram. Int.* **37**(8), 2997–3004 (2011)
53. H. He, W. Lu, J.A.S. Oh, Z. Li, X. Lu, K. Zeng, L. Lu, *ACS Appl. Mater. Interfaces* **12**(27), 30548–30556 (2020)
54. P. Li, Y. Huan, W. Yang, F. Zhu, X. Li, X. Zhang, B. Shen, J. Zhai, *Acta Mater.* **165**, 486–495 (2019)
55. J. Yin, Y. Wang, Y. Zhang, B. Wu, J. Wu, *Acta Mater.* **158**, 269–277 (2018)

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